



**浩畅半导体**  
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**M28S** TRANSISTOR (NPN)

**SOT-23 Plastic-Encapsulate Transistors**

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客户确认：

公司签章：

部门

工程部

品保部

采购部

签名

日期



**SOT-23 Plastic-Encapsulate Transistors**

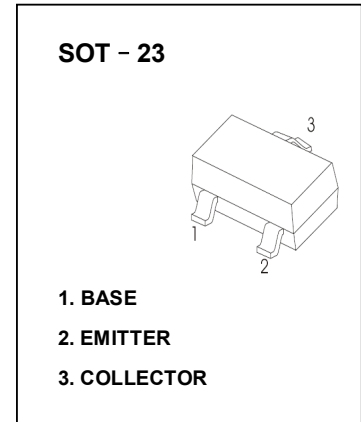
**M28S** TRANSISTOR (NPN)

**FEATURES**

- Excellent  $h_{FE}$  Linearity
- High DC Current Gain

**MAXIMUM RATINGS ( $T_a=25^\circ\text{C}$  unless otherwise noted)**

Symbol	Parameter	Value	Unit
$V_{CBO}$	Collector-Base Voltage	40	V
$V_{CEO}$	Collector-Emitter Voltage	20	V
$V_{EBO}$	Emitter-Base Voltage	6	V
$I_C$	Collector Current	1	A
$P_C$	Collector Power Dissipation	200	mW
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	625	$^\circ\text{C}/\text{W}$
$T_j$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature	-55~+150	$^\circ\text{C}$



**ELECTRICAL CHARACTERISTICS ( $T_a=25^\circ\text{C}$  unless otherwise specified)**

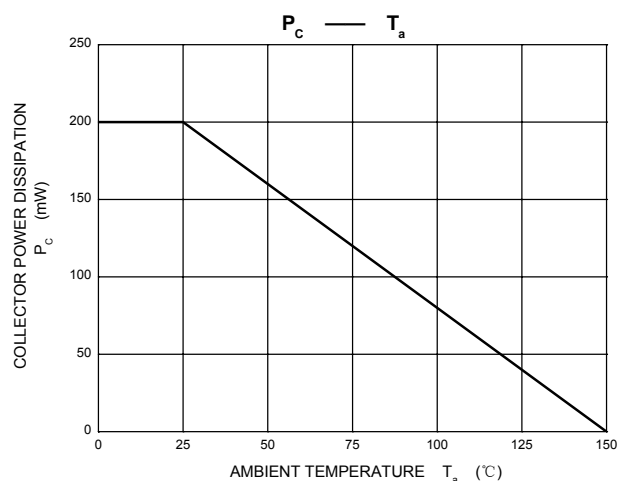
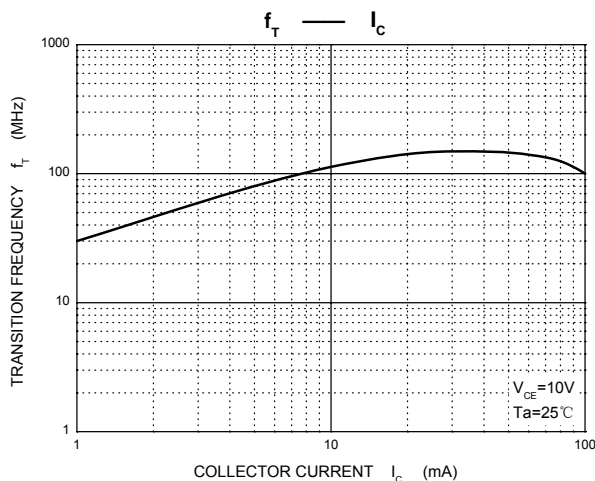
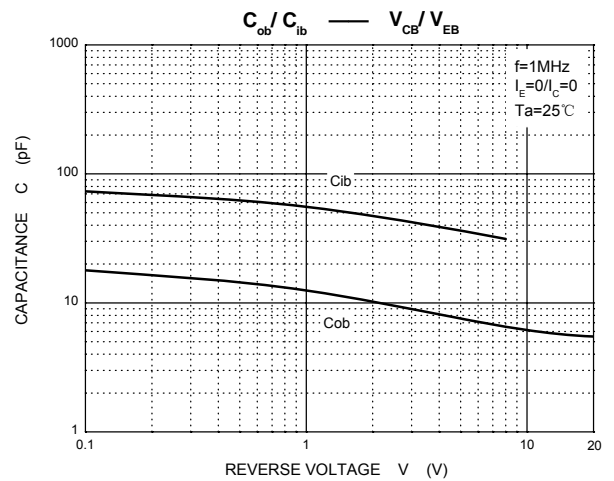
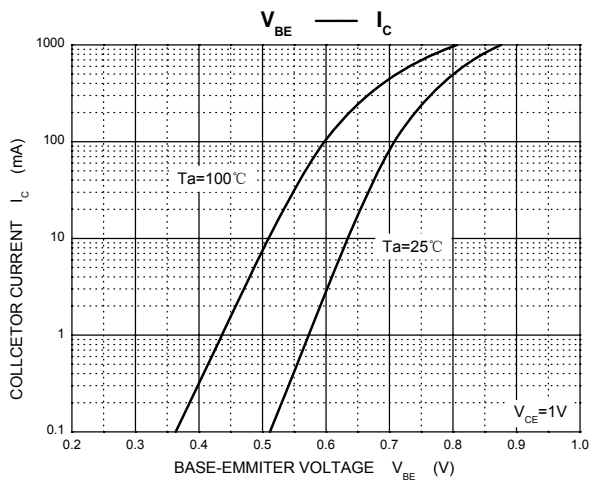
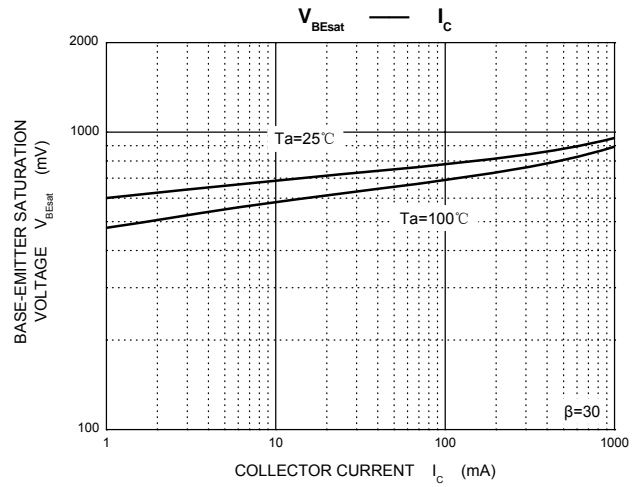
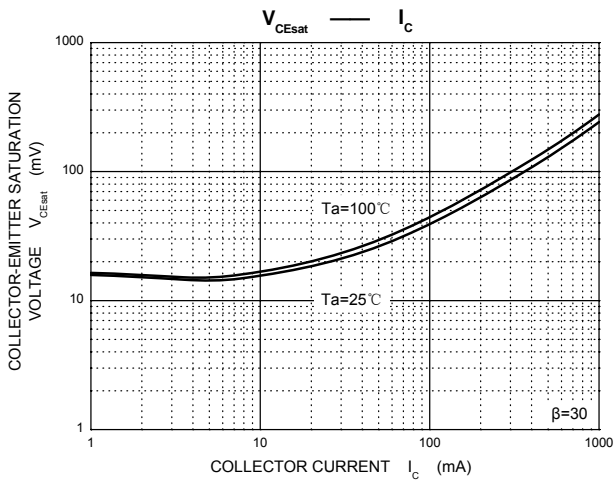
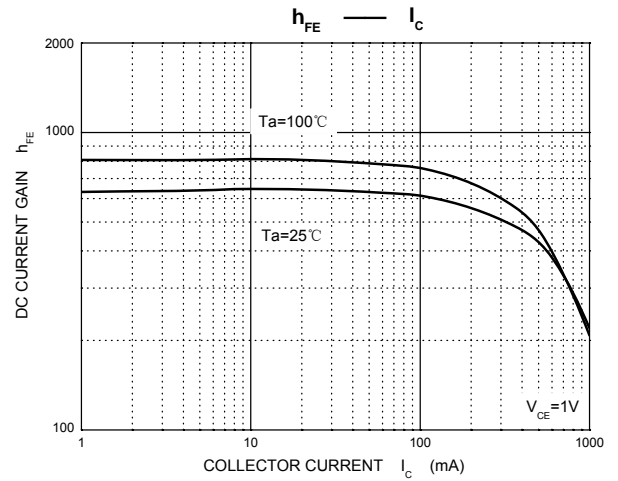
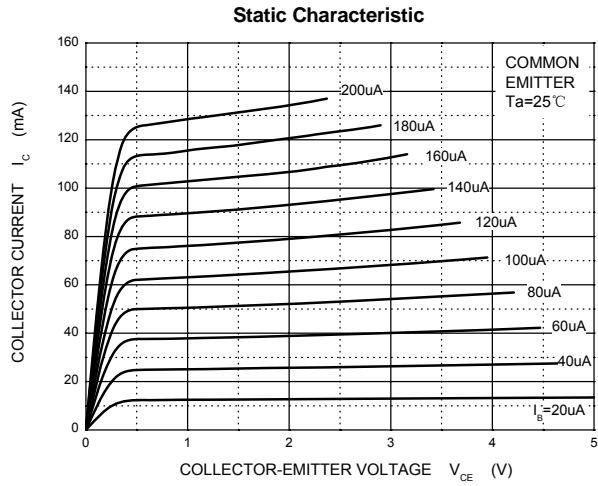
Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=0.1\text{mA}, I_E=0$	40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1\text{mA}, I_B=0$	20			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=0.1\text{mA}, I_C=0$	6			V
Collector cut-off current	$I_{CBO}$	$V_{CB}=35\text{V}, I_E=0$			0.1	$\mu\text{A}$
Collector cut-off current	$I_{CEO}$	$V_{CE}=20\text{V}, I_B=0$			5	$\mu\text{A}$
Emitter cut-off current	$I_{EBO}$	$V_{EB}=5\text{V}, I_C=0$			0.1	$\mu\text{A}$
DC current gain	$h_{FE(1)}$	$V_{CE}=1\text{V}, I_C=1\text{mA}$	290			
	$h_{FE(2)}$	$V_{CE}=1\text{V}, I_C=100\text{mA}$	300		1000	
	$h_{FE(3)}$	$V_{CE}=1\text{V}, I_C=300\text{mA}$	300			
	$h_{FE(4)}$	$V_{CE}=1\text{V}, I_C=500\text{mA}$	300			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=600\text{mA}, I_B=20\text{mA}$			0.55	V
Transition frequency	$f_T$	$V_{CE}=10\text{V}, I_E=50\text{mA}, f=1\text{MHz}$	100			MHz
Collector output capacitance	$C_{ob}$	$V_{CB}=10\text{V}, I_E=0, f=1\text{MHz}$		9		pF

**CLASSIFICATION OF  $h_{FE(2)}$**

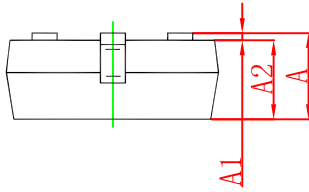
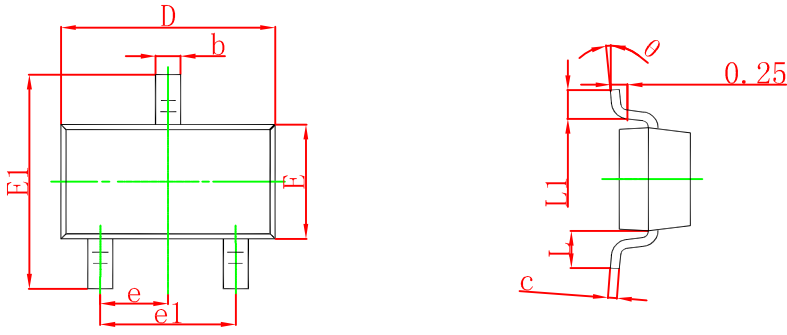
RANK	B	C	D
RANGE	300 - 550	500 - 700	650 - 1000
MARKING	28S		

# Typical Characteristics

# M28S

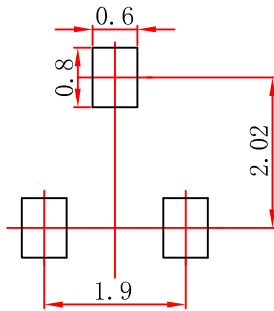


## SOT-23 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

## SOT-23 Suggested Pad Layout



### Note:

1. Controlling dimension: in millimeters.
2. General tolerance:  $\pm 0.05$  mm.
3. The pad layout is for reference purposes only.